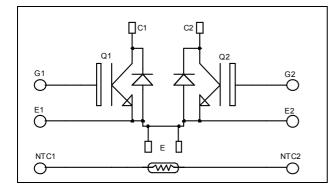


# Dual common source Trench + Field Stop IGBT3 Power Module



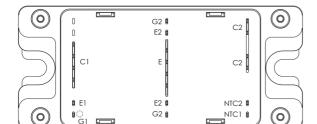
 $V_{CES} = 600V$  $I_{C} = 100A$  @ Tc = 80°C

#### **Application**

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

#### **Features**

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
  - High level of integration
- Internal thermistor for temperature monitoring



#### **Benefits**

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

#### Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		600	V
Ţ	Continuous Collector Current	$T_C = 25^{\circ}C$	150	
$I_{\rm C}$	Continuous Conector Current	$T_C = 80$ °C	100	A
$I_{CM}$	Pulsed Collector Current	$T_C = 25$ °C	200	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Maximum Power Dissipation	$T_C = 25$ °C	340	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	200A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

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## All ratings @ $T_j = 25$ °C unless otherwise specified

### **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				250	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		1.5	1.9	V
$V_{CE(sat)}$	Conector Emitter Saturation Voltage	$I_{\rm C} = 100 A$	$T_j = 150$ °C		1.7		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1.5 \text{ mA}$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V$ , $V_{CE} = 0V$				400	nA

**Dynamic Characteristics** 

·	Characteristic	Test Conditions	Min	Typ	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		6100		
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$		390		pF
$C_{res}$	Reverse Transfer Capacitance	f = 1MHz		190		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		115		
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$		45		
$T_{d(off)}$	Turn-off Delay Time	$V_{\text{Bus}} = 300 \text{V}$ $I_{\text{C}} = 100 \text{A}$		225		ns
$T_{\mathrm{f}}$	Fall Time	$R_G = 3.3\Omega$		55		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C)		130		
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$		50		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 300V$ $I_{C} = 100A$		300		ns
$T_{\rm f}$	Fall Time	$R_G = 3.3\Omega$		70		
Б	Turn on Engage	$V_{GE} = \pm 15V$ $T_j = 25^{\circ}C$		0.4		mJ
Eon	Turn on Energy	$V_{\text{Bus}} = 300 \text{V}$ $T_{\text{j}} = 150 ^{\circ} \text{C}$		0.875		1113
Е	Turn off Energy	$I_C = 100A$ $T_j = 25^{\circ}C$		2.5		m I
$E_{off}$	Turn off Energy	$R_G = 3.3\Omega$ $T_j = 150^{\circ}C$		3.5		mJ

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			600			V
$I_{RM}$	Maximum Reverse Leakage Current	V <sub>R</sub> =600V	$T_i = 25^{\circ}C$ $T_i = 150^{\circ}C$			250 500	μΑ
$I_{\mathrm{F}}$	DC Forward Current		$Tc = 80^{\circ}C$		100		A
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_{\rm F} = 100 A$	$T_i = 25^{\circ}C$		1.6	2	V
V F	Diode Forward Voltage	$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.5		·
+	Reverse Recovery Time		$T_j = 25^{\circ}C$		125		no
$t_{rr}$	Reverse Recovery Time	$T_{\rm j} = 150^{\circ}{\rm C}$	$T_{\rm j} = 150^{\circ}{\rm C}$		220		ns
	Daviana Dagayany Changa	$I_{\rm F} = 100 A$	$T_j = 25$ °C		4.7		C
$Q_{rr}$	Reverse Recovery Charge	$V_R = 300V$ di/dt = 2000A/µs	$T_{i} = 150^{\circ}C$		9.9		μC
Е	D D E		$T_j = 25$ °C		1.1		ma I
$E_{r}$	Reverse Recovery Energy		$T_{i} = 150^{\circ}C$		2.4		mJ



Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

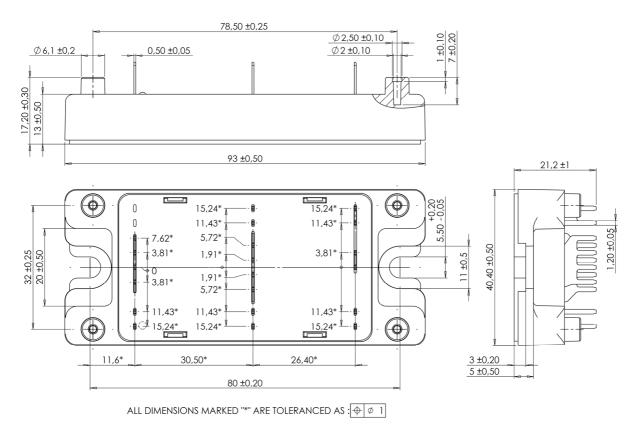
Symbol	Characteristic	Min	Тур	Max	Unit	
R <sub>25</sub>	Resistance @ 25°C		50		kΩ	
${ m B}_{25/85}$	$T_{25} = 298.15 \text{ K}$		3952		K	

$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature R<sub>T</sub>: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance		IGBT			0.44	4 °C/W
RthJC			Diode			0.77	C/ VV
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
$T_{J}$	Operating junction temperature range		-40		175		
$T_{STG}$	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature		-40		100		
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight				160	g	

#### SP4 Package outline (dimensions in mm)

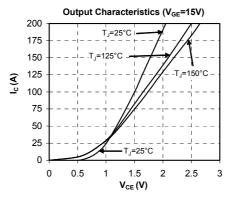


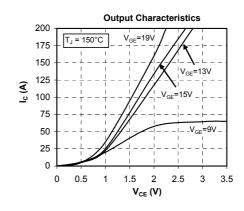
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

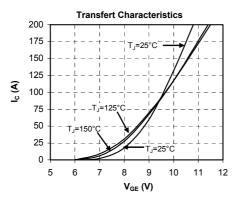
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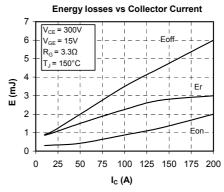


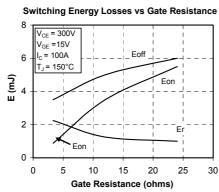
### **Typical Performance Curve**

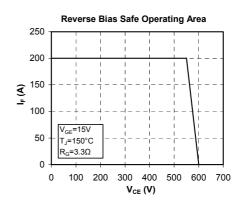


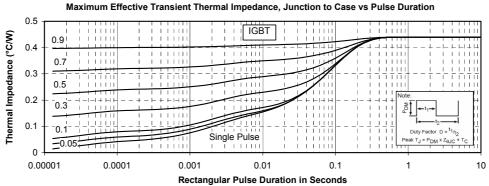




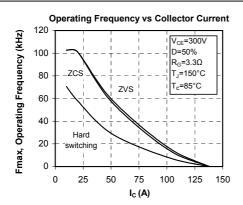


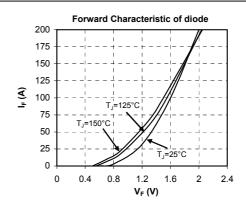


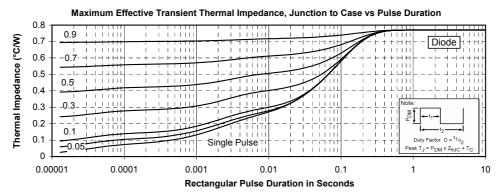












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